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Substitute for Form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete If Known		
				Application Number	101812,703	
				Filing Date	3/30/04	
				First Named Inventor	Park et al.	
				Group Art Unit	2814	
Examiner Name	A. Chambliss					
Sheet	1	of	1	Attorney Docket No.	AF01221	

U.S. PATENT DOCUMENTS						
Exam. Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
AC	AA	5,773,343		Lee et al.	06/30/1998	Entire Document
AC	AB	6,225,173	B1	Yu	05/01/2001	Entire Document
	AC					
	AD					
	AF					
	AG					

FOREIGN PATENT DOCUMENTS								
Exam. Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Office ³	Number ⁴	Kind Code ² (if known)				
	BA							
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Exam. Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
AC	CA	"A Novel 0.1µm MOSFET Structure with Inverted Sidewall and Recessed Channel", JEONGHO LYU, BYUNG-GOOK PARK, KUKJIN CHUN and JONG DUK LEE, IEEE Electron Device Letters, volume 17, No. 4, April, 1996, pp. 157-159.	
AC	CB	"Short-Channel Effect Immunity and Current Capability of Sub-0.1-Micron MOSFET's Using a Recessed Channel", PAUL-HANRI BRICOUT and EMMANUEL DUBOIS, IEEE Transactions on Electron Devices, Volume 43, No. 8, August, 1996, pp.1251-1255.	
AC	CC	"The Investigation of Recessed Channel SOI Devices", XING ZHANG, RU HUANG, XUEMEI XI, MANSUN CHAN PING K. KO and YANGYUAN WANG, IEEE, 1998, pp. 720-723.	
	CD		
	CE		
	CF		
	CG		
	CH		

Examiner Signature	<i>A. Chambliss</i>	Date Considered	2/6/06
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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